NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLX92A** is Designed for transmitting applications in class-A, B or C with a supply voltage up to 28 V

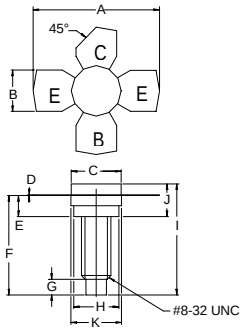
FEATURES:

- High Gain - 11.0 dB Min.
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

I_C	0.7 A
V_{CB}	65 V
P_{DISS}	6.0 W @ T_C = 25 °C
T_J	-65 to +200 °C
T_{STG}	-65 to +150 °C
θ_{JC}	9.8 °C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 10 mA	65			V
BV_{CES}	I_C = 10 mA	65			V
BV_{CEO}	I_C = 25 mA	33			V
BV_{EBO}	I_E = 1.0 mA	4.0			V
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	10			---
f_T	V_{CE} = 5.0 V I_C = 100 mA		1.2		GHz
C_c	V_{CB} = 10 V f = 1.0 MHz		6.5		pF
C_e	V_{EB} = 0 V f = 1.0 MHz		25		pF
P_G η_C	V_{CE} = 28 V P_{OUT} = 2.5 W f = 470 MHz	11 60			dB %